

SEMICONDUCTOR TECHNICAL DATA

KTD1003

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH CURRENT APPLICATION.

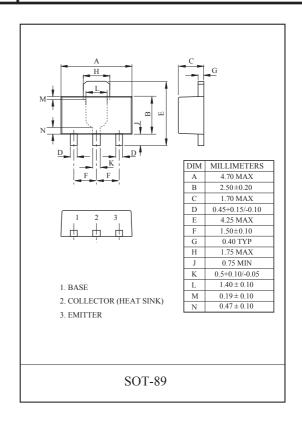
FEATURES

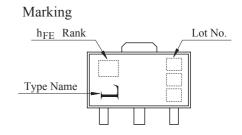
- · High DC Current Gain
 - : $h_{FE}=800 \sim 3200$. ($V_{CE}=5.0V$, $I_{C}=300$ mA).
- · Wide Area of Safe Operation.
- · Low Collector Saturation Voltage
 - : $V_{CE(sat)}$ =0.17V (I_C =500mA, I_B =5.0mA).

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	V _{CBO}	60	V	
Collector-Emitter Voltage	V _{CEO}	50	V	
Emitter-Base Voltage	$V_{\rm EBO}$	8	V	
Collector Current	I_{C}	1.0	A	
Collector Power Dissipation	P _C	500	mW	
	P _C *	1	W	
Junction Temperature	T _j	150	${\mathbb C}$	
Storage Temperature Range	T_{stg}	-55~150	${\mathbb C}$	

P_C*: KTD1003 Mounted on Ceramic Substrate (250mm²x0.8t)

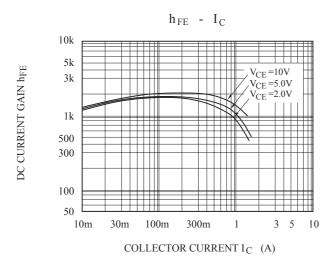


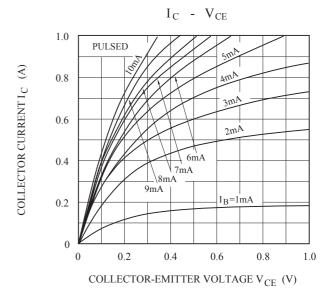


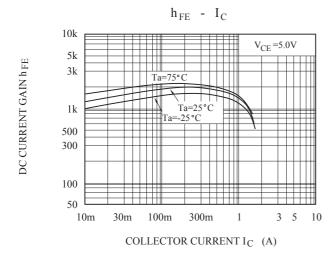
ELECTRICAL CHARACTERISTICS (Ta=25°C)

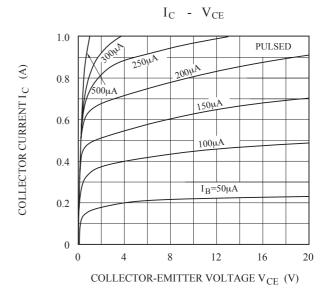
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V_{CB} =60V, I_{E} =0	-	-	100	nA
Emitter Cut-off Current	I _{EBO}	$V_{EB}=8V$, $I_{C}=0$	-	-	100	nA
DC Current Gain	h _{FE} (1) Note	$V_{CE} = 5.0V, I_{C} = 300 \text{mA}$	800	1500	3200	
	h _{FE} (2)	$V_{CE} = 5.0V, I_{C} = 1.0A$	400	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I_{C} =500mA, I_{B} =5.0mA	-	0.17	0.30	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I_{C} =500mA, I_{B} =5.0mA	-	0.80	1.2	V
Collector Output Capacitance	C _{ob}	$V_{CB}=10V$, $I_{E}=0$, $f=1.0MHz$	-	18	30	pF
Transition Frequency	f_T	$V_{CE}=10V$, $I_{C}=500$ mA, $f=100$ MHz	150	250	-	MHz
Base-Emitter Voltage	$V_{ m BE}$	$V_{CE}=5V$, $I_{C}=100$ mA	-	630	700	mV

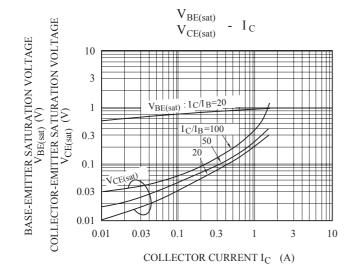
Note: h_{FE} Classification A:800 ~ 1600, B:1200 ~ 2400, C:2000 ~ 3200











KTD1003

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- 2. When you intend to use these products with equipment or device which require an extremely high of reliability and special applications (such as automobile, air travel aerospace, transportation equipment, life support, system and safety devices) in which special quality and reliability and the failure or malfunction of products may directly jeopardize or harm the human body or damage to property and any application other than the standard application intended, please be sure to consult with our sales representative in advance.
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